NSN 5961-01-372-1078

Unitized Semiconductor Devices - Page 1 of 1

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Inclosure Material:

Ceramic

End Application:

Alr62 f111d/e

Component Name And Quantity:

6 transistor

Mounting Method:

Terminal

Features Provided:

Burn in and electrostatic sensitive

Semiconductor Material:

Silicon single transistor

Voltage Rating In Volts Per Characteristic:

60.0 breakdown voltage, collector-to-emitter, base open single transistor and 60.0 breakdown voltage, collector-to-base, emitter open single transistor and 5.0 breakdown voltage, emitter-to-base, collector open single transistor

Current Rating Per Characteristic:

10.00 microamperes zero-gate-voltage source current preset single transistor

Power Rating Per Characteristic:

720.0 milliwatts small-signal input power, common-collector absolute single transistor

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius ambient air

Test Data Document:

15786-325726 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

14 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0